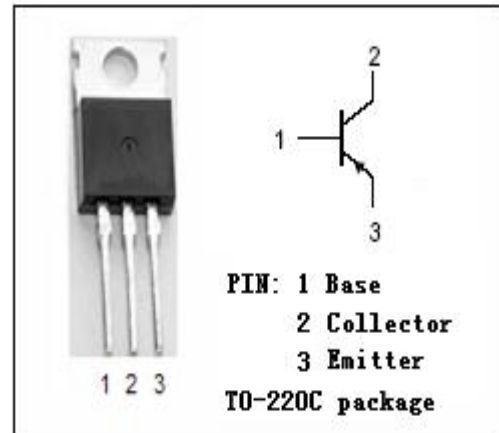


isc Silicon PNP Power Transistor
BD240/A/B/C
DESCRIPTION

- DC Current Gain $-h_{FE} = 40(\text{Min})@ I_C = -0.2\text{A}$
- Collector-Emitter Sustaining Voltage-
: $V_{CEO(\text{SUS})} = -45\text{V}(\text{Min})$ - BD240; $-60\text{V}(\text{Min})$ - BD240A
 $-80\text{V}(\text{Min})$ - BD240B; $-100\text{V}(\text{Min})$ - BD240C
- Complement to Type BD239/A/B/C
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

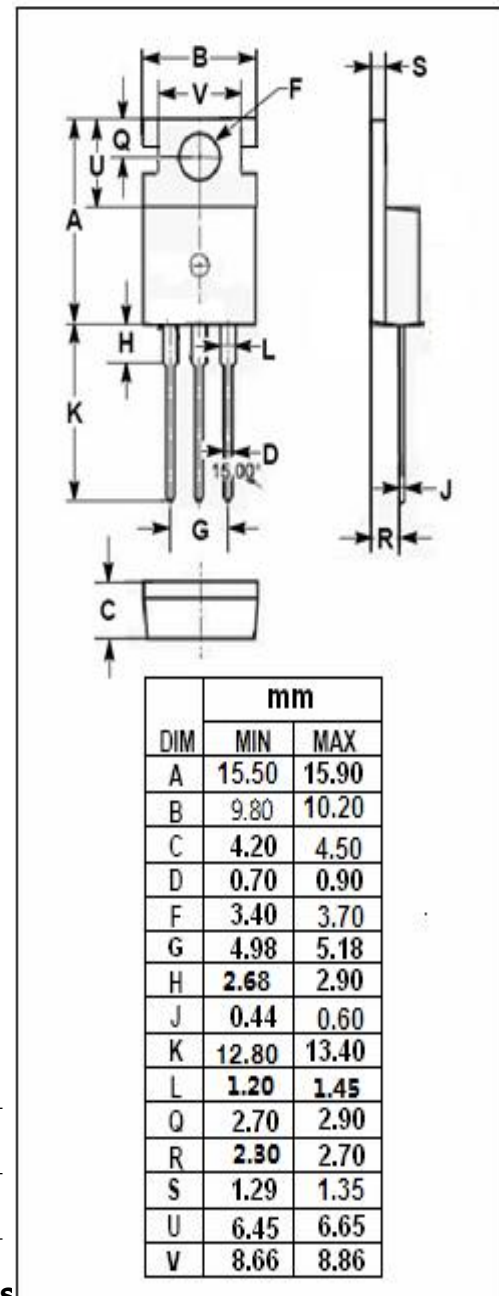
- Designed for medium power linear and switching application


ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT	
V_{CER}	Collector-Emitter Voltage	BD240	-55	V
		BD240A	-70	
		BD240B	-90	
		BD240C	-115	
V_{CEO}	Collector-Emitter Voltage	BD240	-45	V
		BD240A	-60	
		BD240B	-80	
		BD240C	-100	
V_{EBO}	Emitter-Base Voltage	-5	V	
I_C	Collector Current-Continuous	-2	A	
I_{CM}	Collector Current-Peak	-4	A	
I_B	Base Current	-0.6	A	
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	30	W	
T_J	Junction Temperature	150	$^\circ\text{C}$	
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{\text{th j-c}}$	Thermal Resistance, Junction to Case	4.17	$^\circ\text{C/W}$



isc Silicon PNP Power Transistor

BD240/A/B/C

ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	BD240	I _C = -30mA; I _B = 0	-45		V
		BD240A		-60		
		BD240B		-80		
		BD240C		-100		
V _{CE(sat)}	Collector-Emitter Saturation Voltage		I _C = -1A; I _B = -0.2A		-0.7	V
V _{BE(on)}	Base-Emitter On Voltage		I _C = -1A; V _{CE} = -4V		-1.3	V
I _{CEs}	Collector Cutoff Current	BD240	V _{CE} = -45V; V _{BE} = 0		-0.2	mA
		BD240A	V _{CE} = -60V; V _{BE} = 0			
		BD240B	V _{CE} = -80V; V _{BE} = 0			
		BD240C	V _{CE} = -100V; V _{BE} = 0			
I _{CEO}	Collector Cutoff Current	BD240/A	V _{CE} = -30V; I _B = 0		-0.3	mA
		BD240B/C	V _{CE} = -60V; I _B = 0			
I _{EBO}	Emitter Cutoff Current		V _{EB} = -5V; I _C =0		-1.0	mA
h _{FE-1}	DC Current Gain		I _C = -0.2A; V _{CE} = -4V	40		
h _{FE-2}	DC Current Gain		I _C = -1A; V _{CE} = -4V	15		

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